

Inchange Semiconductor

Product Specification

Silicon PNP Darlington Power Transistors

2SB1626

DESCRIPTION

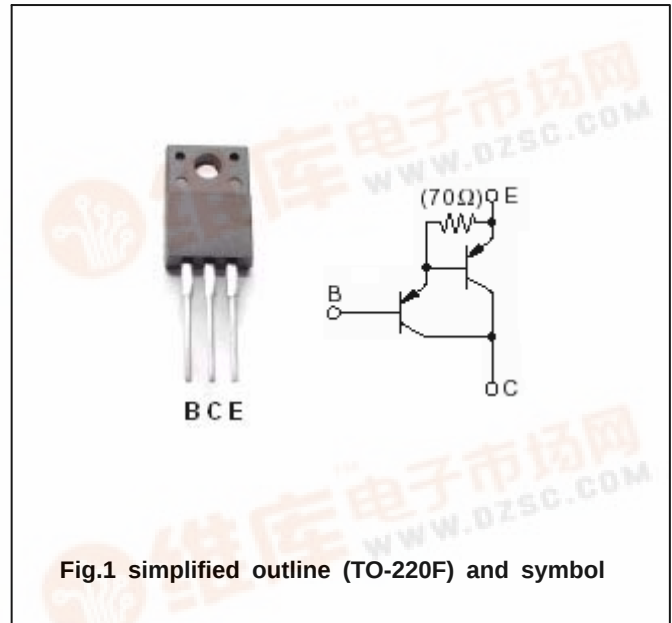
- With TO-220F package
- Complement to type 2SD2495

APPLICATIONS

- For audio, series regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-110	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-6	A
I_B	Base current		-1	A
P_C	Collector dissipation	$T_C=25$	30	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -50mA$; $I_B = 0$	-110			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -5A$; $I_B = -5mA$			-2.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -5A$; $I_B = -5mA$			-3.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -110V$; $I_E = 0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V$; $I_C = 0$			-0.1	mA
h_{FE}	DC current gain	$I_C = -5A$; $V_{CE} = -4V$	5000			
f_T	Transition frequency	$I_C = -0.5A$; $V_{CE} = -12V$		100		MHz
C_{OB}	Collector output capacitance	$f = 1MHz$; $V_{CB} = -10V$		110		pF

Switching times

t_{on}	Turn-on time	$I_C = -5A$ $I_{B1} = -I_{B2} = -5mA$ $V_{CC} = 30V$, $R_L = 6\Omega$	1.1		μs
t_s	Storage time		3.2		μs
t_f	Fall time		1.1		μs

◆ h_{FE} Classifications

O	p	Y
5000-12000	6500-20000	15000-30000

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PACKAGE OUTLINE

